## **YJ Planar Fast Recovery Diode Die Specification**

600V 30A, Fast recovery diode die based on silicon planar process

Part No.: FRD30A600AS-290M

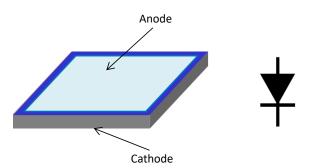
## **Main Products Characterstics**

• Average forward current: IF(AV) = 30A

• Maximum operating junction temperature: Tj = 150 °C

Planar Construction

· Top metal: Al



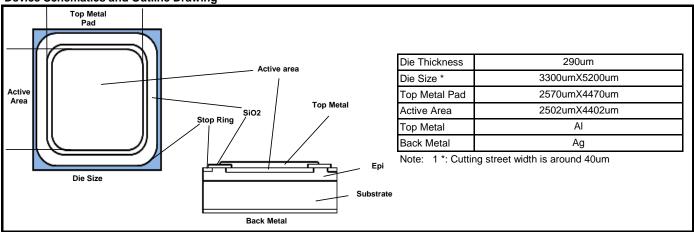
**Maximum Ratings** 

Parameter	Symbol	Rating			
Repetitive peak reverse voltage	$V_{RRM}$	600V			
Average forward current	I <sub>F(AV)</sub>	30A			
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I <sub>FSM</sub>	300A			
Storage temperature range	T <sub>stg</sub>	-40 to +150 °C			
Maximum operating junction temperature	T <sub>j</sub>	150 °C			

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
Faranietei	Symbol	Spec	Typical
Reverse breakdown voltage $I_R = 50$ uA	$V_{BR}$	630V	680V
Maximum forward voltage drop $I_F$ = 20A, Pulse Test: tp = 380 $\mu s, \ \delta \leqslant 2\%$	$V_{F}$	1.45V	1.25V
Reverse Recovery Time $I_F=0.5A$ , $I_R=1A$ , $I_{rr}=0.25A$	Trr	50ns	40ns
$\begin{aligned} &\text{Maximum reverse current} & \ V_{\text{R}} = V_{\text{RRM}} \\ &\text{Pulse Test: tp = 10 ms}, \ \delta \leqslant 2\% \end{aligned}$	I <sub>R</sub>	2uA	0.05uA

**Device Schematics and Outline Drawing** 



## **Important Notice**

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.

All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.